

NPN small signal transistor

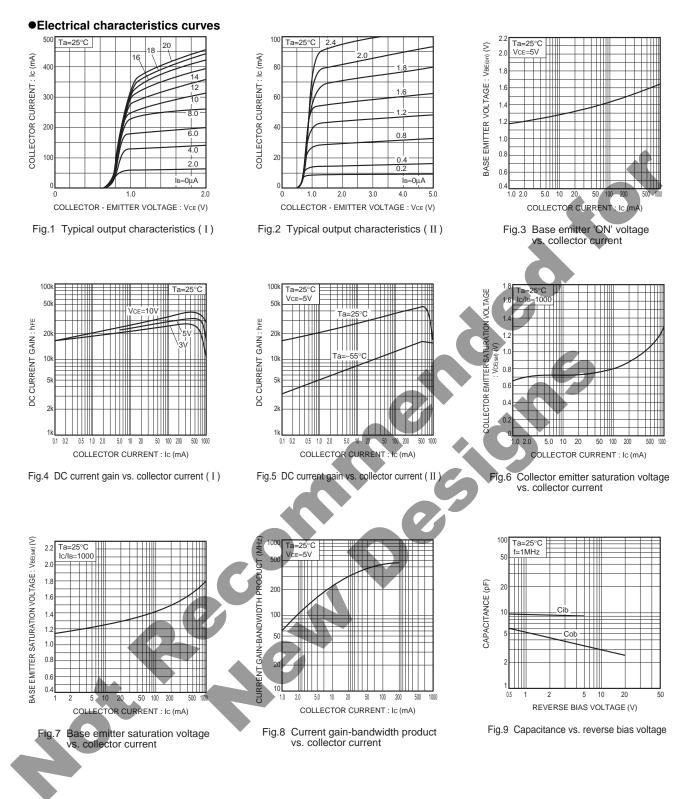
SSTA13

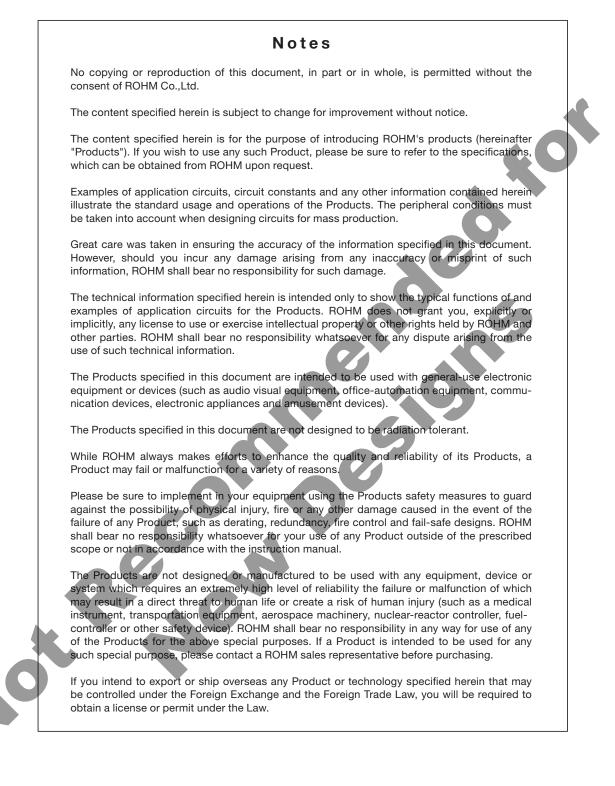
Features Dimensions (Unit : mm) (1) High Current Gain. SSTA13 Packaging specifications Package Taping Туре Code T116 0.15 Basic ordering unit (pieces) 3000 (1)Em Each lead has same dimensions SSTA13 \bigcirc (2)Ba Abbreviated symbol : R1M Absolute maximum ratings (Ta=25°C) Unit Parameter Symbol Limits Vсво 30 Collector-base voltage Collector-emitter voltage Vces 30 Emitter-base voltage Vево 10 Collector current lc 0.3 Collector power dissipation Pc Ŵ 0.2 °C Тj 150 Junction temperature Storage temperature Tstg -55 to 125 °C Electrical characteristics (Ta=25°C) Symbol Min. Max Parameter Unit Conditions Тур. Collector-emitter breakdown voltage **BV**CES 30 V Ic= 100µA _ Collector-emitter breakdown voltage BVCEO 30 V Ic= 10µA _ Emitter-base breakdown voltage BVEBO 10 V Iε= 10μA _ Collector-base cutoff current Ісво μΑ Vcb= 30V 0.1 Emitter-base cutoff current EBC 0.1 VEB= 10V μΑ

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Collector-emitter saturation voltage	VCE(sat)	-	-	1.5	V	Ic/I _B = 100mA/ 0.1mA
Base-emitter voltage	VBE(on)	-	-	2.0	V	Vce= 5V, Ic= 100mA *
DC current transfer ratio	hfe	5000	-	-	-	Vce= 5V, Ic= 10mA
		10000	-	-		Vce= 5V, Ic= 100mA *
Transition frequency	f⊤	125	-	_	MHz	Vce= 5V, Ie= 10mA, f=100MHz
Collector output capacitance	Cob	_	5.4	_	pF	Vсв= 10V, f=100kHz, IE=0
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